

C P W T I Si I

2N3055(NPN), MJ2955(PNP)

15 AMPERE
POWER TRANSISTORS
COMPLEMENTARY SILICON
60 VOLTS, 115 WATTS

Complementary silicon power transistors are designed for general purpose switching and amplifier applications.

Features

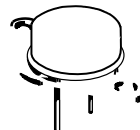
DC Current Gain $h_{FE} = 20 - 70 @ I_C = 4 \text{ A dc}$

Collector-Emitter Saturation Voltage

$V_{CE(sat)} = 1.1 \text{ Vdc (Max) @ } I_C = 4 \text{ A dc}$

Excellent Safe Operating Area

Pb-Free Packages are Available*



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Emitter Voltage	V_{CER}	70	Vdc
Collector-Base Voltage	V_{CB}	100	Vdc
Emitter-Base Voltage	V_{EB}	7	Vdc
Collector Current – Continuous	I_C	15	A dc
Base Current	I_B	7	A dc
Total Power Dissipation @ $T_C = 25 \text{ C}$ Derate Above 25 C	P_D	115 0.657	W W/ C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

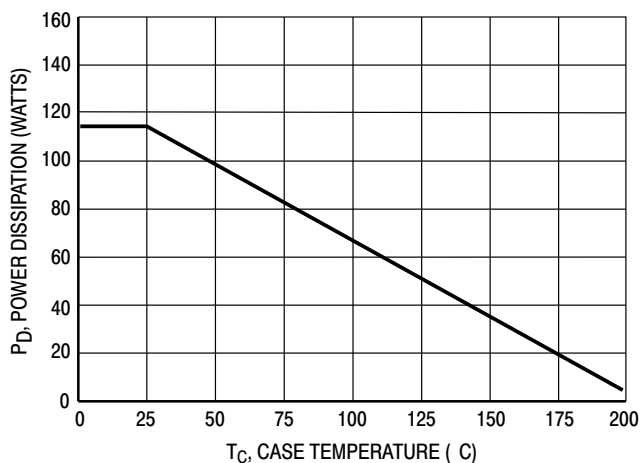


Figure 1. Power Derating

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ORDERING INFORMATION

Device	Package	Shipping
2N3055	TO-204AA	100 Units / Tray
MJ2955G	TO-204AA (Pb-Free)	

Preferred devices are recommended choices for future use and best overall value.

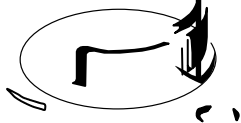
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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.52	

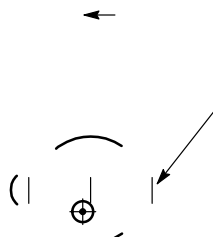
E6: 1. A E 2. E E CASE: C EC	E7: 1. A DE 2. E CASE: CA DE	E8: 1. CA DE #1 2. CA DE #2 CASE: A DE	E9: 1. A DE #1 2. A DE #2 CASE: CA DE
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TO-204 (TO-3)



S A 1:1

E8
 1. D E A D E A C E A
 14.5, 1982.
 2. C D E : C
 3. A E A D E A CA ED
 EFE E CED -204AA E A



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